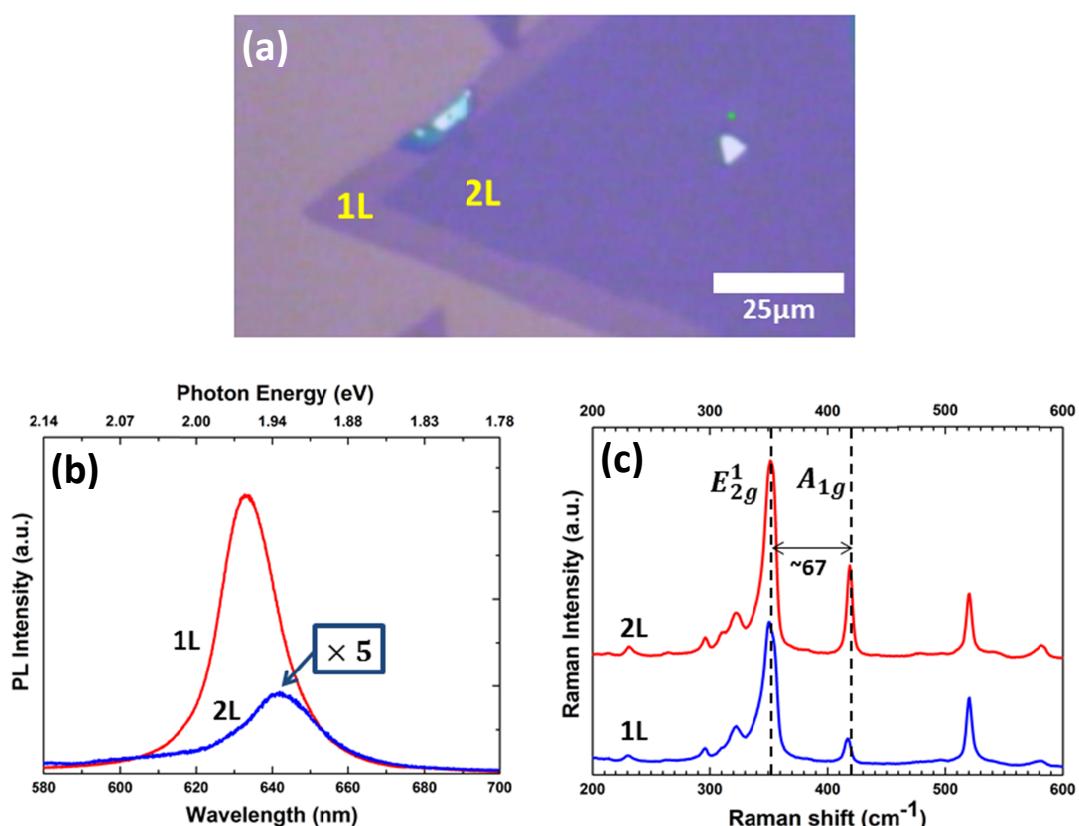
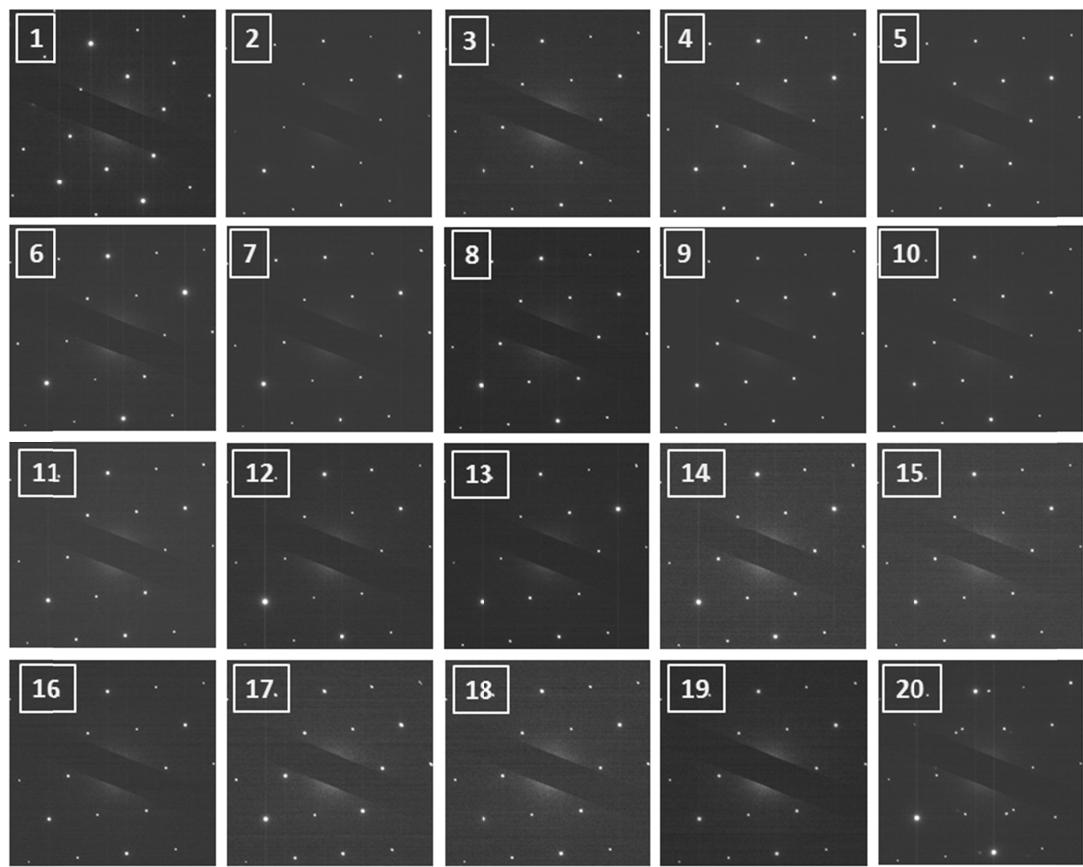


## Supplementary Information

In Fig. S1b, it is evident that the PL intensity of a bi-layer  $\text{WS}_2$  is already quenched significantly with regard to the monolayer. Apart from the enhanced intensity at the  $A_{1g}$  peak, the bi-layer  $\text{WS}_2$  has characteristic  $E_{2g}^1/A_{1g}$  peak difference slightly greater than monolayer  $\text{WS}_2$  as demonstrated in Fig. S1c, which agrees proportionally with Ref 17.



**Fig. S1** PL and Raman characterization of  $\text{WS}_2$  monolayer (1L) and bi-layer (2L) domains. (a) Optical image of the as-examined  $\text{WS}_2$  domain. (b and c) Characteristic PL and Raman profiles of the corresponding 1L and 2L  $\text{WS}_2$  domains indicated in (a).



**Fig. S2** Full exhibition of SAED patterns of the as-produced WS<sub>2</sub> domain taken from 20 consecutive SiN TEM holes highlighted in Fig.5 (main text).